

DATA SHEET

BUT11; BUT11A Silicon diffused power transistors

Product specification
Supersedes data of February 1996
File under Discrete Semiconductors, SC06

1997 Aug 13

Silicon diffused power transistors

BUT11; BUT11A

DESCRIPTION

High-voltage, high-speed, glass-passivated NPN power transistor in a TO-220AB package.

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor control systems.

PINNING

PIN	DESCRIPTION
1	base
2	collector; connected to mounting base
3	emitter

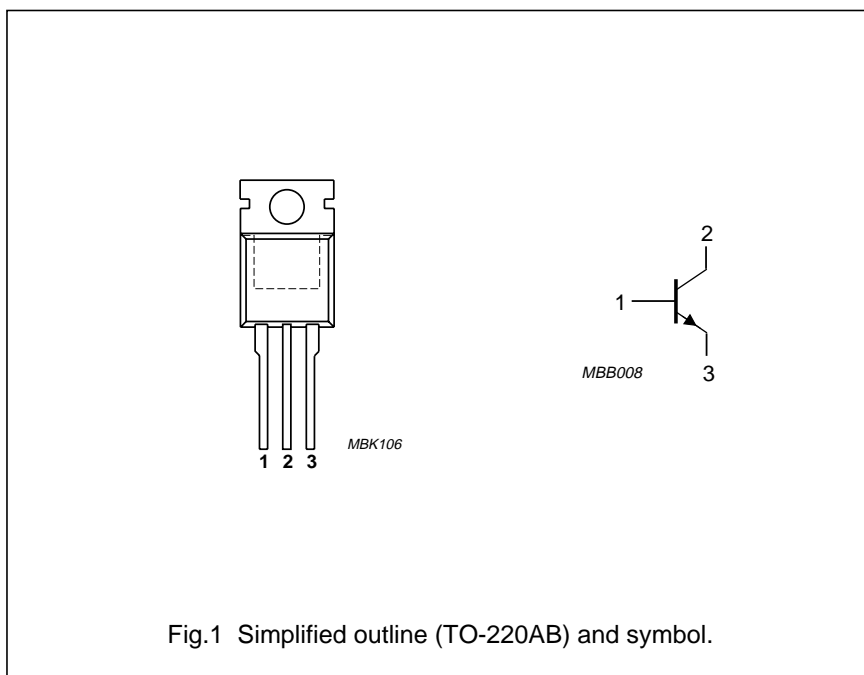


Fig.1 Simplified outline (TO-220AB) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0	850	V
	BUT11			
V _{CEO}	collector-emitter voltage	open base	400	V
	BUT11A			
V _{CEsat}	collector-emitter saturation voltage	see Figs 7 and 9	1.5	V
I _C	collector current (DC)	see Figs 2 and 4	5	A
I _{CM}	collector current (peak value)	see Fig. 4	10	A
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C; see Fig.3	100	W
t _f	fall time	resistive load; see Figs 11 and 12	0.8	μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-mb}	thermal resistance from junction to mounting base	1.25	K/W

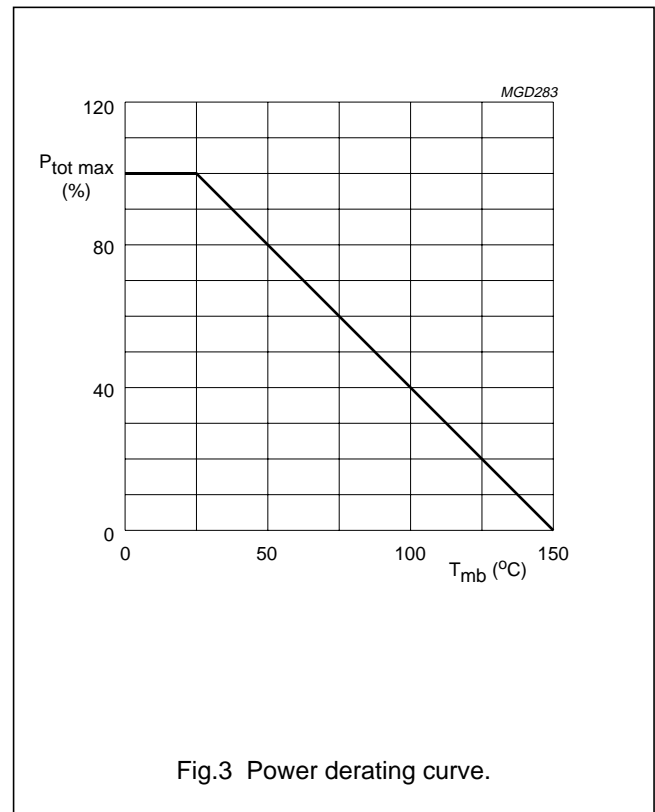
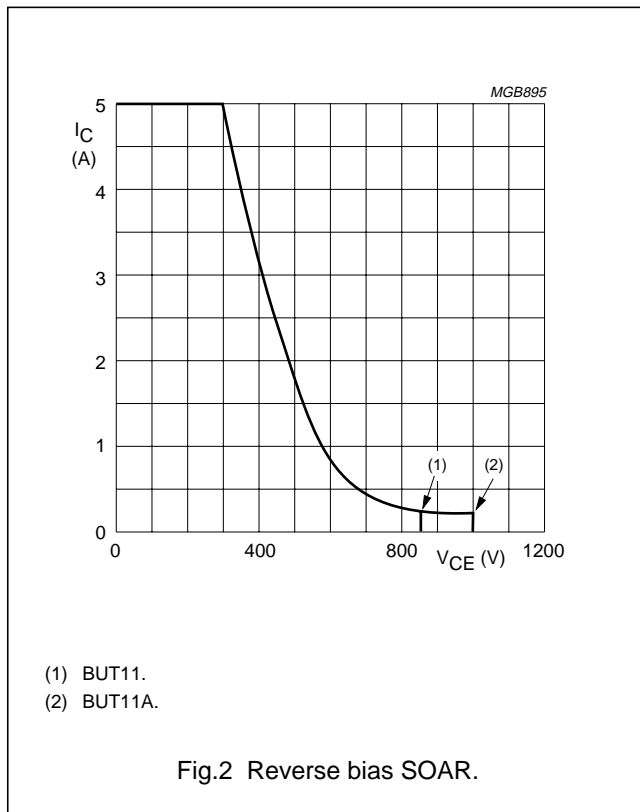
Silicon diffused power transistors

BUT11; BUT11A

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0$	-	850	V
	BUT11			1000	V
V_{CEO}	collector-emitter voltage	open base	-	400	V
	BUT11A			450	V
I_C	collector current (DC)	see Figs 2 and 4	-	5	A
I_{CM}	collector current (peak value)	$t_p < 2$ ms; see Fig. 4	-	10	A
I_B	base current (DC)		-	2	A
I_{BM}	base current (peak value)	$t_p < 2$ ms	-	4	A
P_{tot}	total power dissipation	$T_{mb} \leq 25$ °C; see Fig.3	-	100	W
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	150	°C



Silicon diffused power transistors

BUT11; BUT11A

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

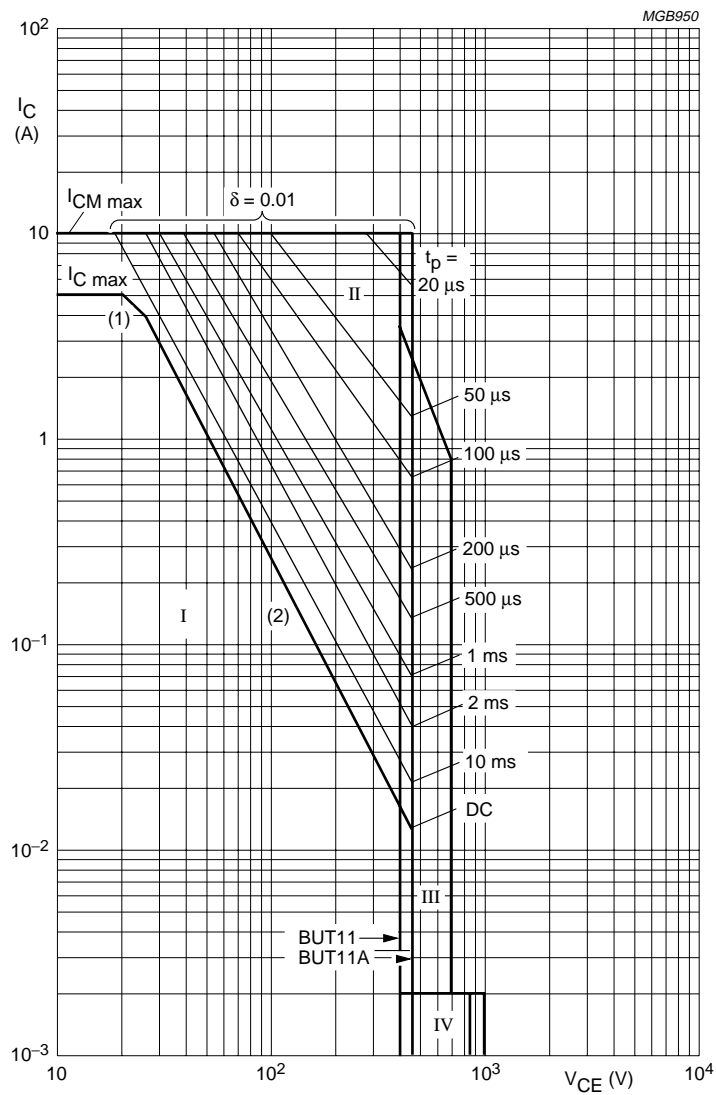
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{CEOsust}$	collector-emitter sustaining voltage BUT11 BUT11A	$I_C = 100\text{ mA}$; $I_{Boff} = 0$; $L = 25\text{ mH}$; see Figs 5 and 6	400	–	–	V
			450	–	–	V
V_{CEsat}	collector-emitter saturation voltage BUT11 BUT11A	$I_C = 3\text{ A}$; $I_B = 600\text{ mA}$; see Figs 7 and 9	–	–	1.5	V
		$I_C = 2.5\text{ A}$; $I_B = 500\text{ mA}$; see Figs 7 and 9	–	–	1.5	V
V_{BEsat}	base-emitter saturation voltage BUT11 BUT11A	$I_C = 3\text{ A}$; $I_B = 0.6\text{ A}$; see Fig.7	–	–	1.3	V
		$I_C = 2.5\text{ A}$; $I_B = 0.5\text{ A}$; see Fig.7	–	–	1.3	V
I_{CES}	collector-emitter cut-off current	$V_{CE} = V_{CESMmax}$; $V_{BE} = 0$; note 1	–	–	1	mA
		$V_{CE} = V_{CESMmax}$; $V_{BE} = 0$; $T_j = 125\text{ °C}$; note 1	–	–	2	mA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 9\text{ V}$; $I_C = 0$	–	–	10	mA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}$; $I_C = 5\text{ mA}$; see Fig.10	10	18	35	
		$V_{CE} = 5\text{ V}$; $I_C = 500\text{ mA}$; see Fig.10	10	20	35	
Switching times resistive load (see Fig.12)						
t_{on}	turn-on time BUT11 BUT11A	$I_{Con} = 3\text{ A}$; $I_{Bon} = -I_{Boff} = 600\text{ mA}$	–	–	1	μs
		$I_{Con} = 2.5\text{ A}$; $I_{Bon} = -I_{Boff} = 500\text{ mA}$	–	–	1	μs
t_s	storage time BUT11 BUT11A	$I_{Con} = 3\text{ A}$; $I_{Bon} = -I_{Boff} = 600\text{ mA}$	–	–	4	μs
		$I_{Con} = 2.5\text{ A}$; $I_{Bon} = -I_{Boff} = 500\text{ mA}$	–	–	4	μs
t_f	fall time BUT11 BUT11A	$I_{Con} = 3\text{ A}$; $I_{Bon} = -I_{Boff} = 600\text{ mA}$	–	–	0.8	μs
		$I_{Con} = 2.5\text{ A}$; $I_{Bon} = -I_{Boff} = 500\text{ mA}$	–	–	0.8	μs
Switching times inductive load (see Fig.14)						
t_s	storage time BUT11	$I_{Con} = 3\text{ A}$; $I_{Bon} = 600\text{ mA}$	–	1.1	1.4	μs
		$I_{Con} = 3\text{ A}$; $I_{Bon} = 600\text{ mA}$; $T_j = 100\text{ °C}$	–	1.2	1.5	μs
	BUT11A	$I_{Con} = 2.5\text{ A}$; $I_{Bon} = 500\text{ mA}$	–	1.1	1.4	μs
		$I_{Con} = 2.5\text{ A}$; $I_{Bon} = 500\text{ mA}$; $T_j = 100\text{ °C}$	–	1.2	1.5	μs
t_f	fall time BUT11	$I_{Con} = 3\text{ A}$; $I_{Bon} = 600\text{ mA}$	–	80	150	ns
		$I_{Con} = 3\text{ A}$; $I_{Bon} = 600\text{ mA}$; $T_j = 100\text{ °C}$	–	140	300	ns
	BUT11A	$I_{Con} = 2.5\text{ A}$; $I_{Bon} = 500\text{ mA}$	–	80	150	ns
		$I_{Con} = 2.5\text{ A}$; $I_{Bon} = 500\text{ mA}$; $T_j = 100\text{ °C}$	–	140	300	ns

Note

1. Measured with a half-sinewave voltage (curve tracer).

Silicon diffused power transistors

BUT11; BUT11A



$T_{mb} \leq 25 \text{ }^\circ\text{C}$.

I - Region of permissible DC operation.

II - Permissible extension for repetitive pulse operation.

III - Area of permissible operation during turn-on in single transistor converters, provided $R_{BE} \leq 100 \text{ } \Omega$ and $t_p \leq 0.6 \text{ } \mu\text{s}$.

IV - Repetitive pulse operation in this region is permissible provided $V_{BE} \leq 0$ and $t_p \leq 5 \text{ ms}$.

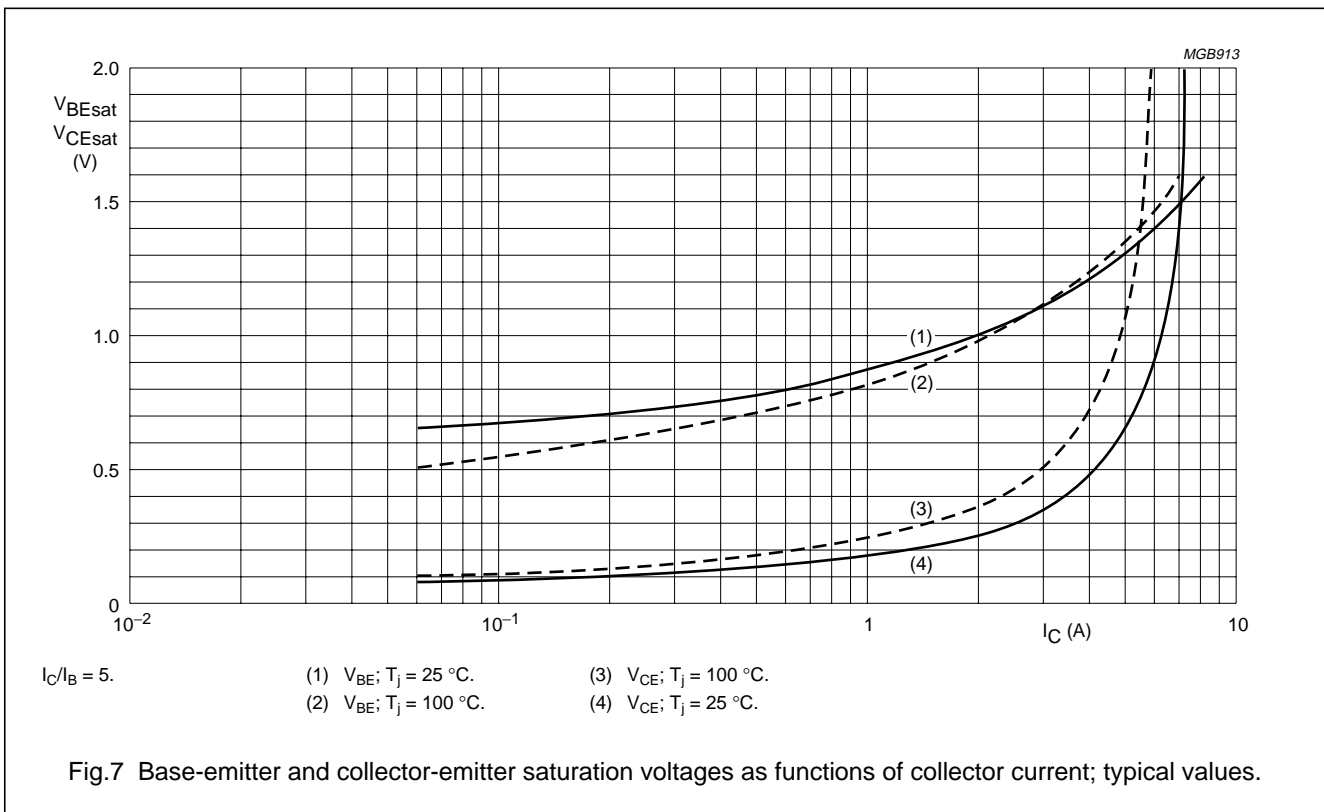
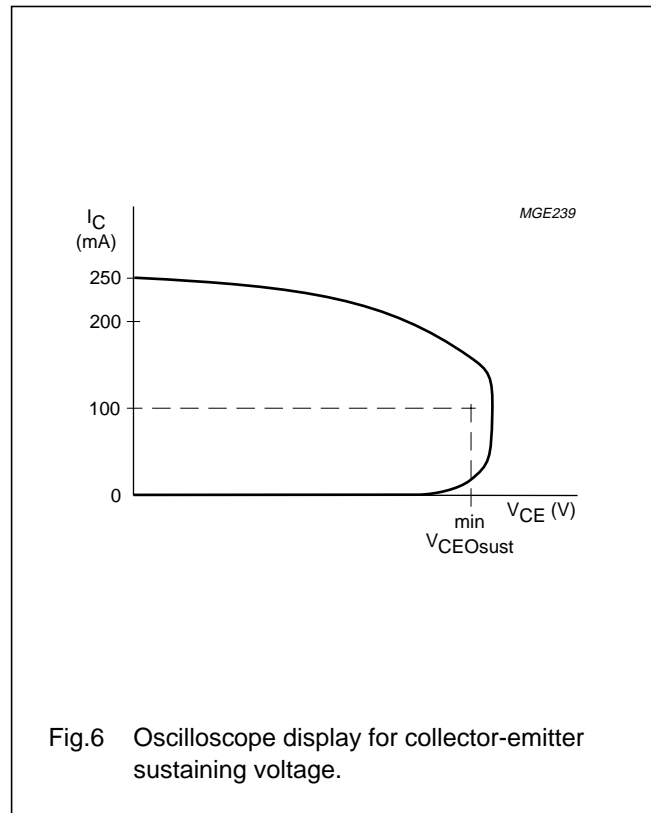
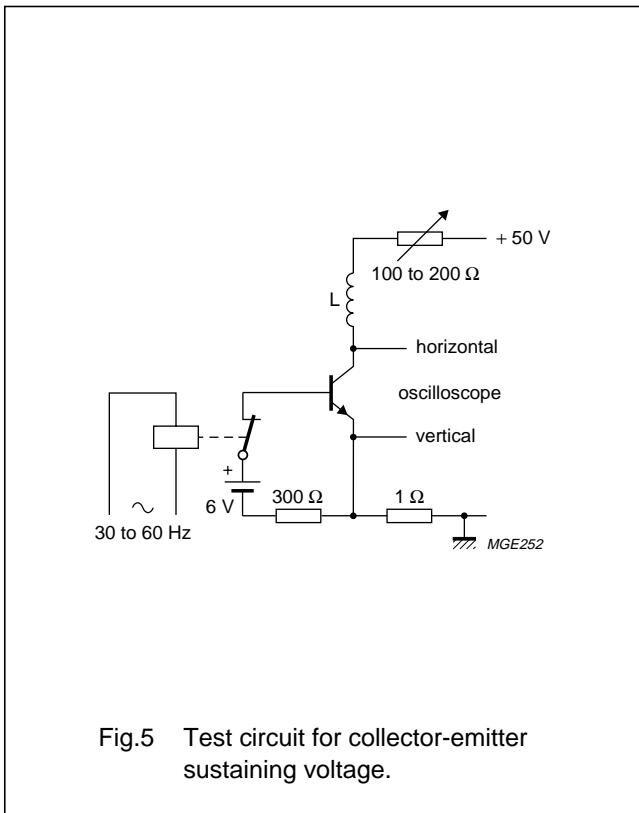
(1) $P_{tot \text{ max}}$ and $P_{tot \text{ peak max}}$ lines.

(2) Second breakdown limits.

Fig.4 Forward bias SOAR.

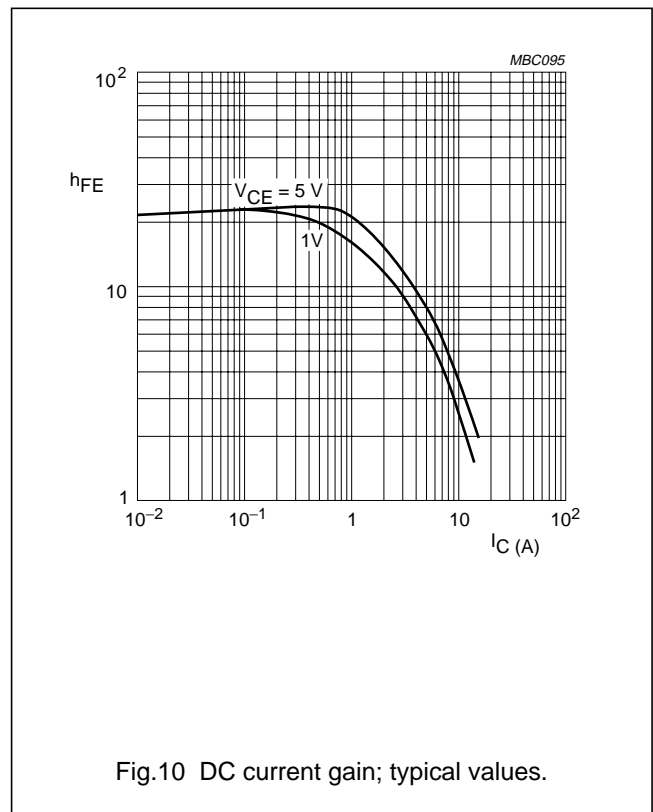
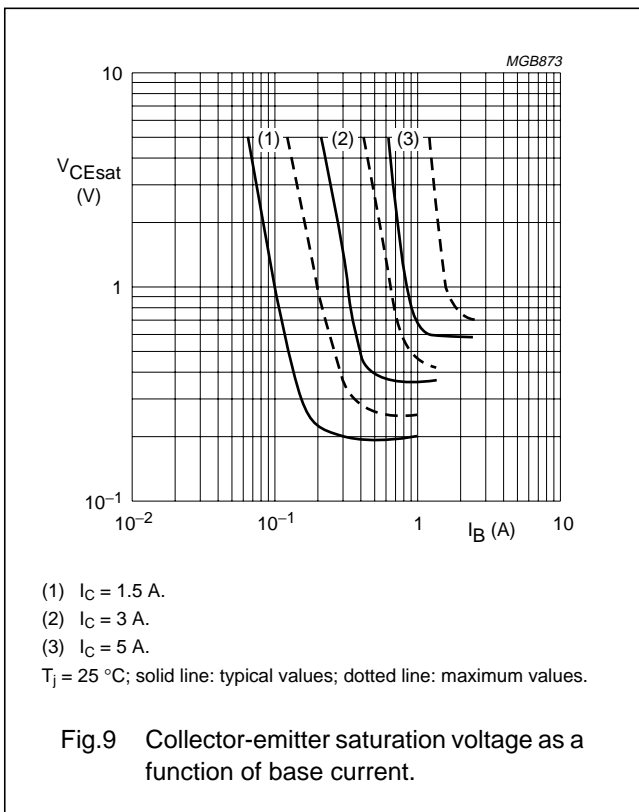
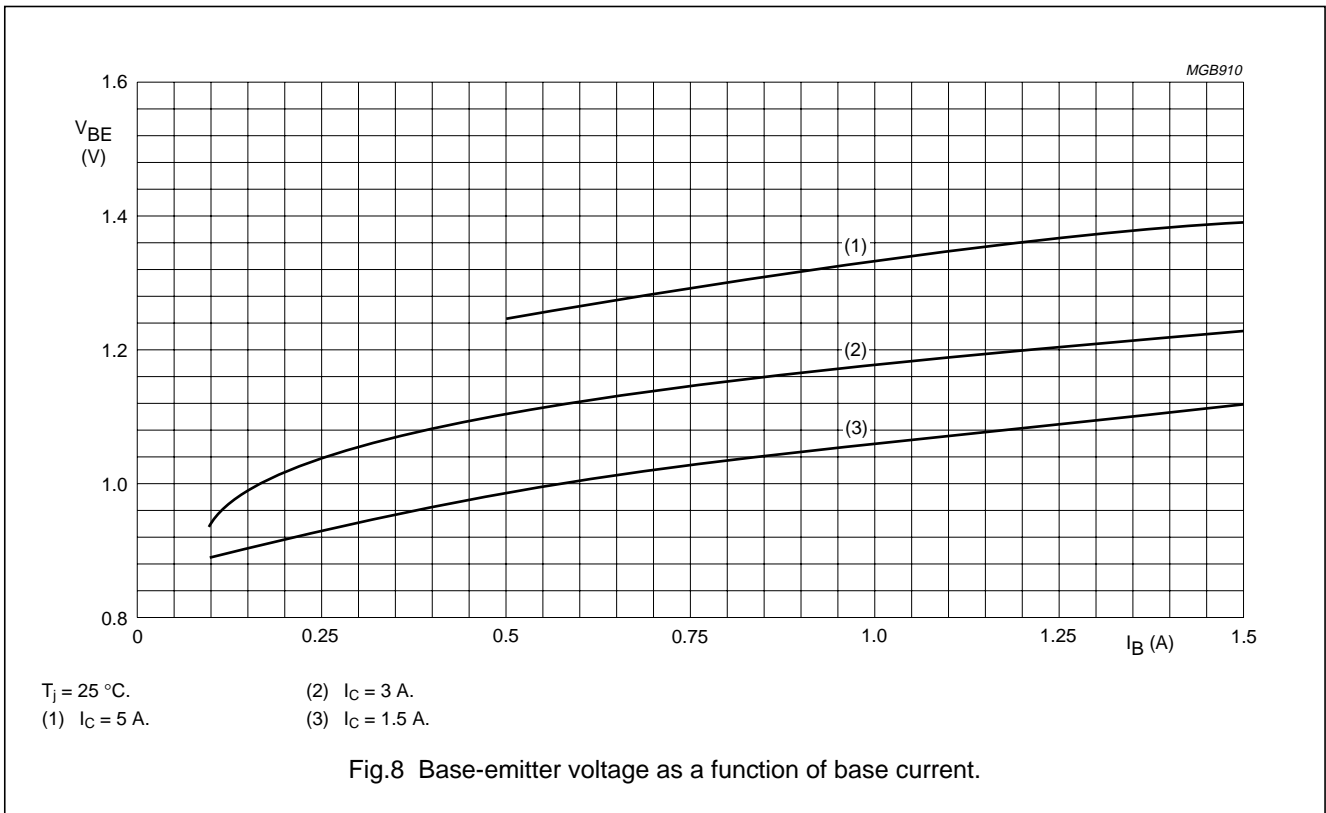
Silicon diffused power transistors

BUT11; BUT11A



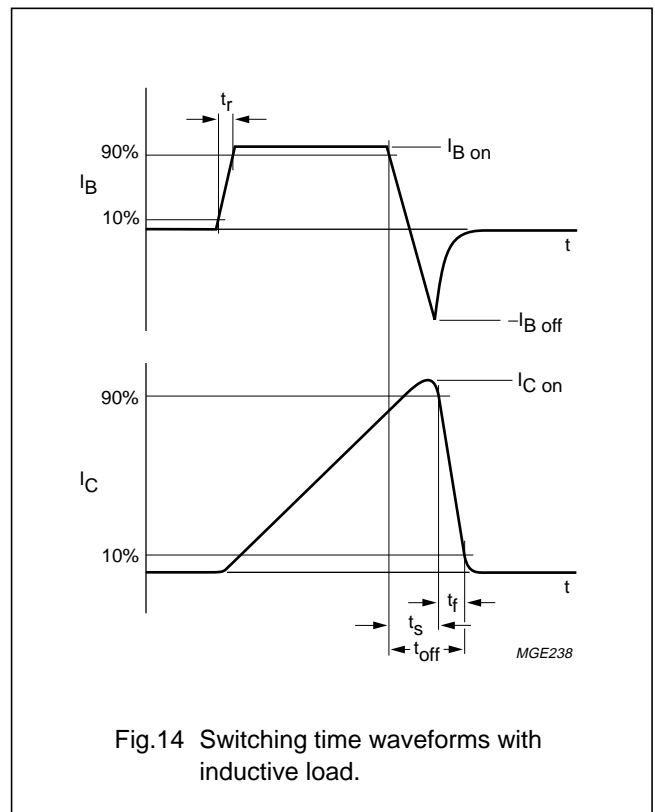
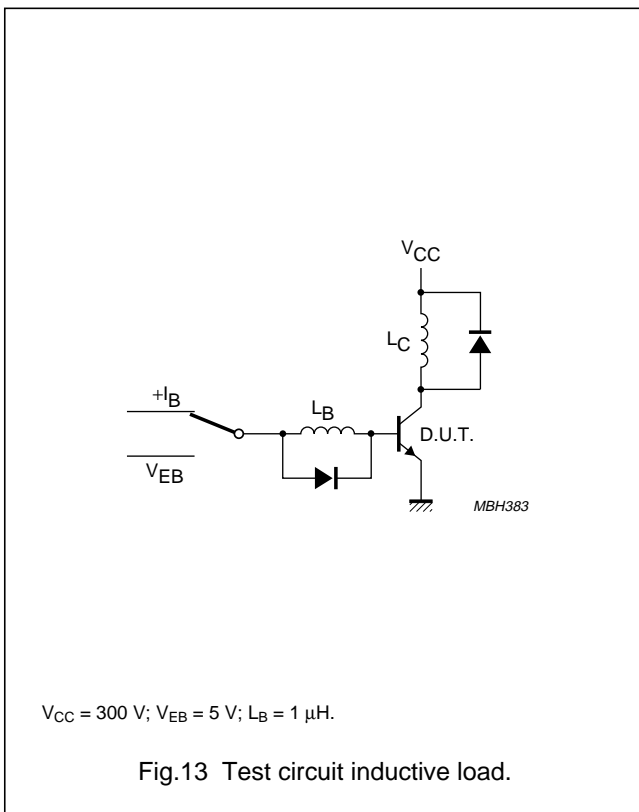
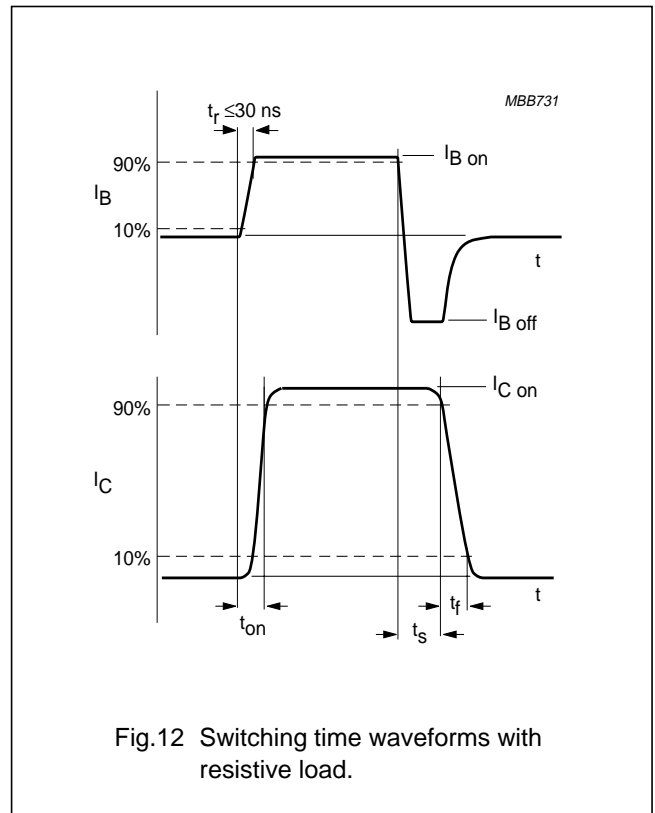
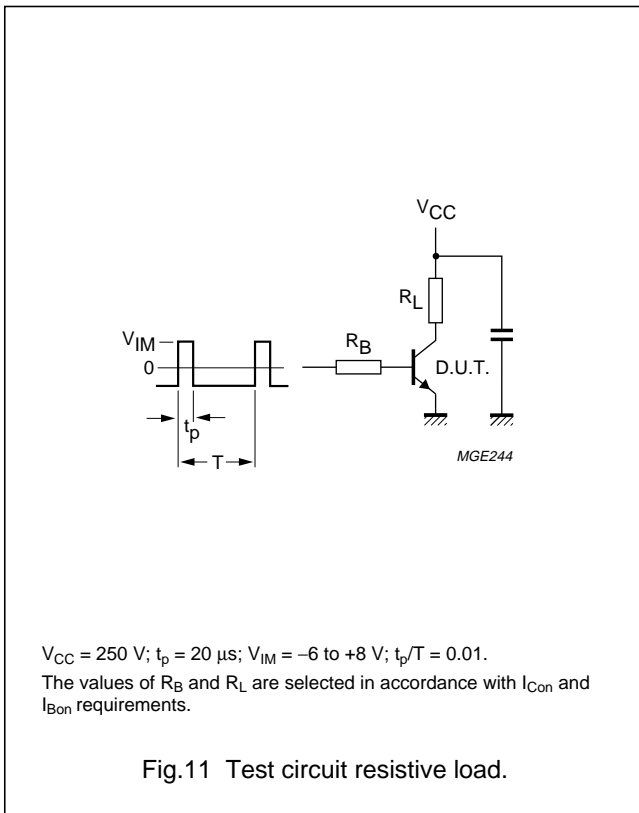
Silicon diffused power transistors

BUT11; BUT11A



Silicon diffused power transistors

BUT11; BUT11A



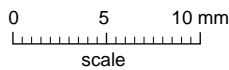
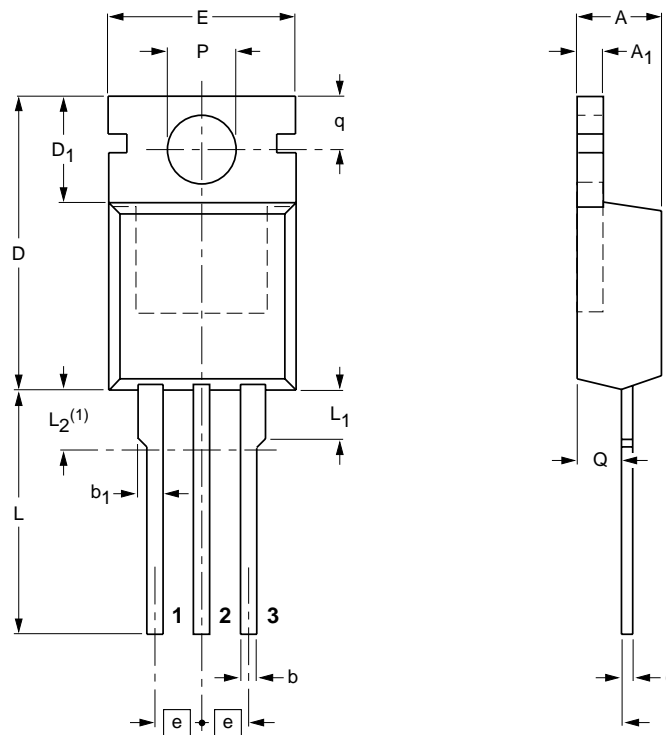
Silicon diffused power transistors

BUT11; BUT11A

PACKAGE OUTLINE

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁	c	D	D ₁	E	e	L	L ₁	L ₂ ⁽¹⁾ max.	P	q	Q
mm	4.5 4.1	1.39 1.27	0.9 0.7	1.3 1.0	0.7 0.4	15.8 15.2	6.4 5.9	10.3 9.7	2.54	15.0 13.5	3.30 2.79	3.0	3.8 3.6	3.0 2.7	2.6 2.2

Note

1. Terminals in this zone are not tinned.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT78		TO-220				97-06-11

Silicon diffused power transistors

BUT11; BUT11A

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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Silicon diffused power transistors

BUT11; BUT11A

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